

MOSFETs Silicon N-Channel MOS (π -MOSVII)

TK8A25DA

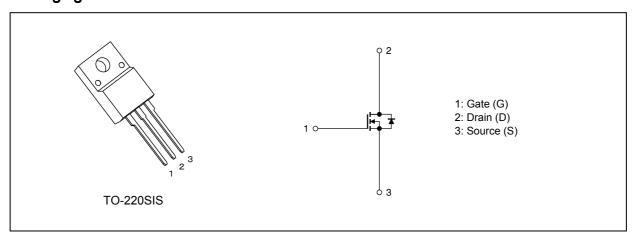
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.41 \Omega$ (typ.)
- (2) Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 250 \text{ V)}$
- (3) Enhancement mode: V_{th} = 1.5 to 3.5 V (V_{DS} = 10 V, I_D = 1 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	250	V
Gate-source voltage		V _{GSS}	±20	7
Drain current (DC)	(Note 1)	I _D	7.5	А
Drain current (pulsed)	(Note 1)	I _{DP}	30	7
Power dissipation	(T _c = 25°C)	P _D	30	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	45	mJ
Avalanche current	(Note 3)	I _{AR}	7.5	А
Reverse drain current (DC)	(Note 1)	I _{DR}	7.5	7
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	30	
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	7
Isolation voltage (RMS)	(t = 1.0 s)	V _{ISO(RMS)}	2000	V
Mounting torque		TOR	0.6	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	4.16	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	62.5	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 50 V, T_{ch} = 25°C (initial), L = 1.33 mH, R_{G} = 25 Ω , I_{AR} = 7.5 A

Note 3: Repetitive rating; pulse width limited by maximum channel temperature

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



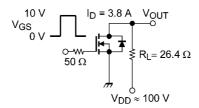
6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μА
Drain cut-off current	I _{DSS}	V _{DS} = 250 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	250	_	_	V
Gate threshold voltage	V_{th}	V _{DS} = 10 V, I _D = 1 mA	1.5	_	3.5	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 3.8 A	_	0.41	0.5	Ω

6.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 100 V, V _{GS} = 0 V, f = 1 MHz	_	550	_	pF
Reverse transfer capacitance	C _{rss}			5.1	_	
Output capacitance	C _{oss}		_	40	_	
Gate resistance	r _g	V _{DS} = OPEN, f = 1 MHz	_	5.8	_	Ω
Switching time (rise time)	t _r	See Figure 6.2.1.		28	_	ns
Switching time (turn-on time)	t _{on}		_	32	_	
Switching time (fall time)	t _f		_	16	_	
Switching time (turn-off time)	t _{off}		_	66		



 $Duty \leq 1\%, \, t_W = 10 \,\, \mu s$

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	$V_{DD} \approx 200 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 7.5 \text{ A}$	ı	16	1	nC
Gate-source charge 1	Q _{gs1}		_	3.3		
Gate-drain charge	Q_{gd}		_	5.3		

6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V_{DSF}	I _{DR} = 7.5 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 7.5 A, V _{GS} = 0 V	_	150	_	ns
Reverse recovery charge	Q _{rr}	-dl _{DR} /dt = 100 A/μs	1	0.8		μС
Peak reverse recovery current	Irr			11	1	Α



7. Marking (Note)

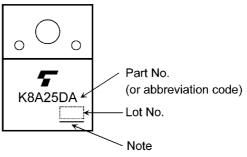


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

8. Characteristics Curves (Note)

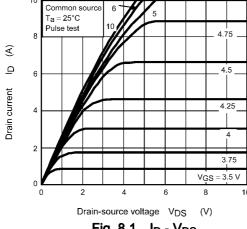


Fig. 8.1 I_D - V_{DS}



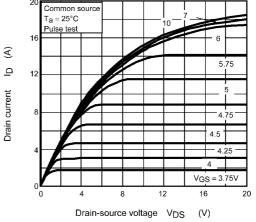


Fig. 8.2 I_D - V_{DS}

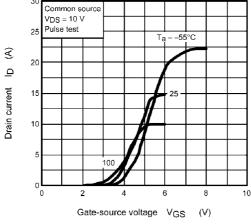


Fig. 8.3 I_D - V_{GS}

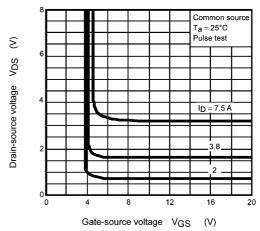


Fig. 8.4 V_{DS} - V_{GS}

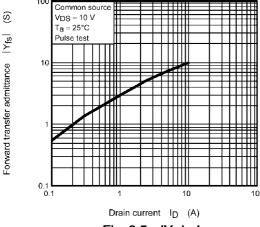


Fig. 8.5 |Y_{fs}| - I_D

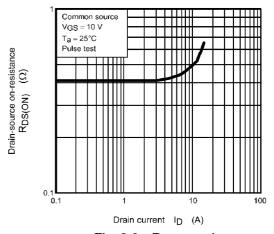


Fig. 8.6 R_{DS(ON)} - I_D

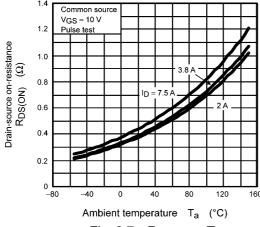


Fig. 8.7 R_{DS(ON)} - T_a

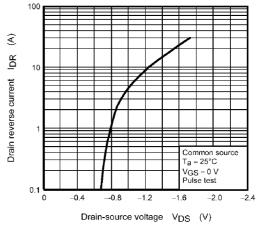


Fig. 8.8 IDR - VDS

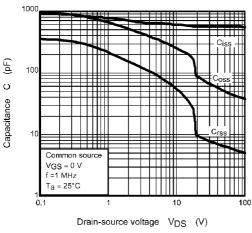


Fig. 8.9 C - V_{DS}

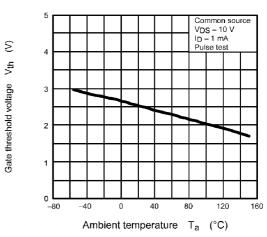


Fig. 8.10 V_{th} - T_a

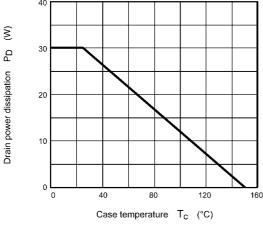


Fig. 8.11 P_D - T_c (Guaranteed Maximum)

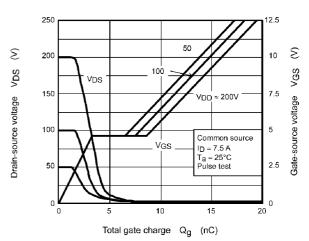


Fig. 8.12 Dynamic Input/Output Characteristics

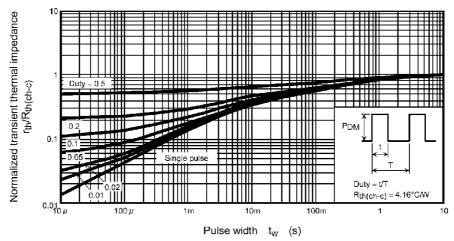


Fig. 8.13 r_{th}/R_{th(ch-c)} - t_w (Guaranteed Maximum)

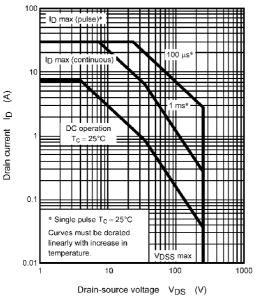


Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

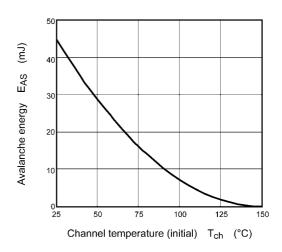


Fig. 8.15 E_{AS} - T_{ch} (Guaranteed Maximum)

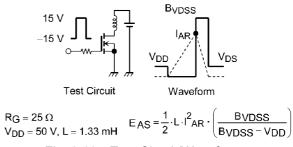


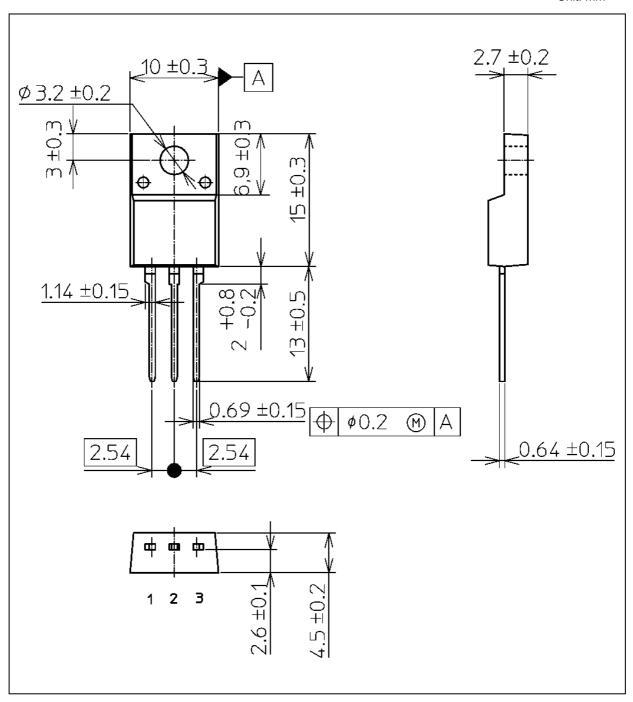
Fig. 8.16 Test Circuit/Waveform

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 1.7 g (typ.)

	Package Name(s)
JEITA: SC-67	
TOSHIBA: 2-10U1S	
Nickname: TO-220SIS	



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BXP7N65D BXP4N65F AOL1454G WMJ80N60C4 BXP2N20L BXP2N65D BXT1150N10J BXT1700P06M TSM60NB380CP ROG

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